

MITSUBISHI IGBT MODULES CM1000DU-34NF

HIGH POWER SWITCHING USE

CM1000DU-34NF



- IC 1000A
- VCES 1700V
- Insulated Type
- 2-elements in a pack

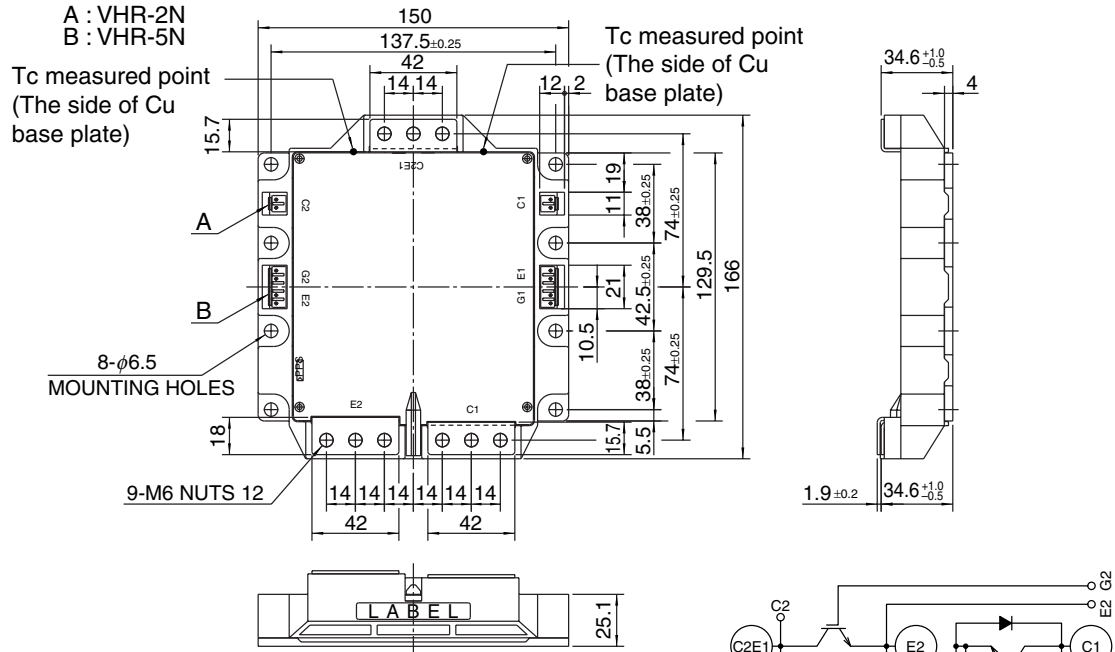
APPLICATION

General purpose inverters Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm

A,B HOUSING Type
(J. S. T. Mfg. Co. Ltd)
A : VHR-2N
B : VHR-5N



CIRCUIT DIAGRAM

Feb. 2009



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MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	1700	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	T _C = 104°C	1000	A
I _{CM}		Pulse (Note 2)	2000	
I _E (Note 1)	Emitter current	T _C = 25°C	1000	A
I _{EM} (Note 1)		Pulse (Note 2)	2000	
P _C (Note 3)	Maximum collector dissipation	T _C = 25°C	8900	W
T _J	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature ^{*3}		-40 ~ +125	°C
V _{iso}	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute	3500	V _{rms}
—	Torque strength	Main terminals M6 screw	3.5 ~ 4.5	N • m
		Mounting M6 screw	3.5 ~ 4.5	N • m
—	Weight	Typical value	1400	g

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{CES}	Collector cutoff current	V _{CE} = V _{CES} , V _{GE} = 0V	—	—	1	mA
V _{GE(th)}	Gate-emitter threshold voltage	I _C = 100mA, V _{CE} = 10V	5.5	7	8.5	V
I _{GES}	Gate leakage current	±V _{GE} = V _{GES} , V _{CE} = 0V	—	—	5	μA
V _{CE(sat)} (chip)	Collector-emitter saturation voltage (without lead resistance)	I _C = 1000A, V _{GE} = 15V (Note 4)	—	2.2	2.8	V
		T _J = 125°C	—	2.45	—	
R _(lead)	Module lead resistance	I _C = 1000A, terminal-chip	—	0.286	—	mΩ
C _{ies}	Input capacitance	V _{CE} = 10V V _{GE} = 0V	—	—	220	nF
C _{oes}	Output capacitance		—	—	25	
C _{res}	Reverse transfer capacitance		—	—	4.7	
Q _G	Total gate charge	V _{CC} = 1000V, I _C = 1000A, V _{GE} = 15V	—	6000	—	nC
t _{d(on)}	Turn-on delay time	V _{CC} = 1000V, I _C = 1000A V _{GE} = ±15V R _G = 0.47Ω, Inductive load	—	—	600	ns
t _r	Turn-on rise time		—	—	150	
t _{d(off)}	Turn-off delay time		—	—	900	
t _f	Turn-off fall time		—	—	200	
t _{rr} (Note 1)	Reverse recovery time		I _E = 1000A	—	—	
Q _{rr} (Note 1)	Reverse recovery charge		—	90	—	μC
V _{EC} (Note 1) (chip)	Emitter-collector voltage (without lead resistance)	I _E = 1000A, V _{GE} = 0V	—	2.3	3	V
R _{th(j-c)Q}	Thermal resistance ^{*1}	IGBT part (1/2 module)	—	—	0.014	K/W
R _{th(j-c)R}		FWDi part (1/2 module)	—	—	0.023	
R _{th(c-f)}	Contact thermal resistance ^{*2}	Case to heat sink, Thermal compound applied (1/2 module)	—	0.016	—	
R _G	External gate resistance		0.47	—	4.7	Ω

Note 1. I_E, V_{EC}, t_{rr} & Q_{rr} represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T_J) does not exceed T_{Jmax} rating.

3. Junction temperature (T_J) should not increase beyond 150°C.

4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

*1 : Case temperature (T_C) measured point is just under the chips.

If you use this value, R_{th(f-a)} should be measured just under the chips.

*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

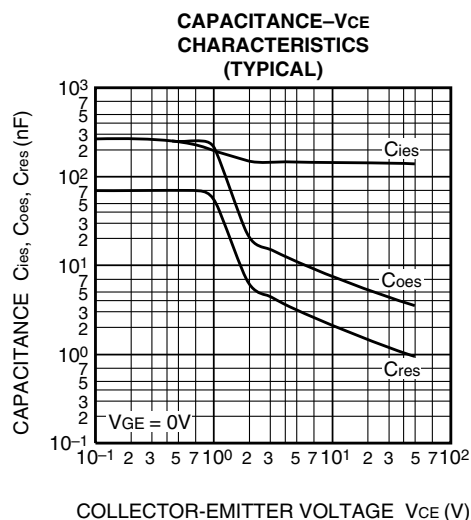
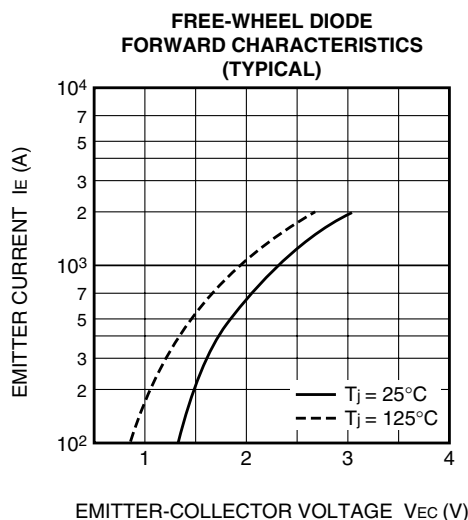
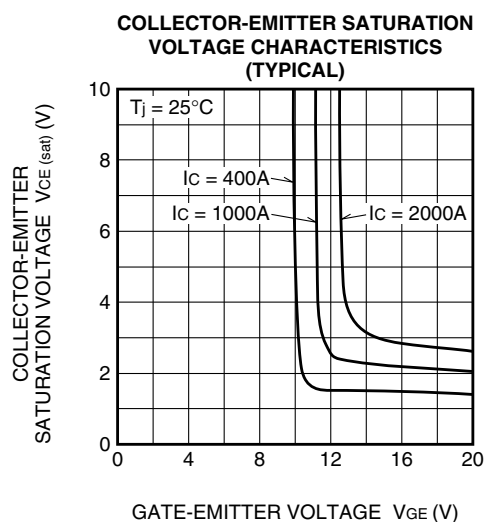
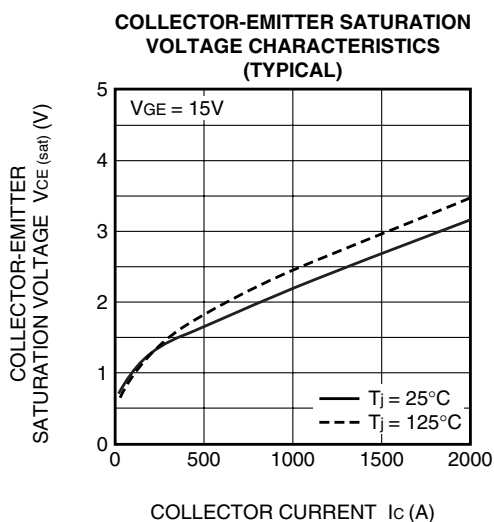
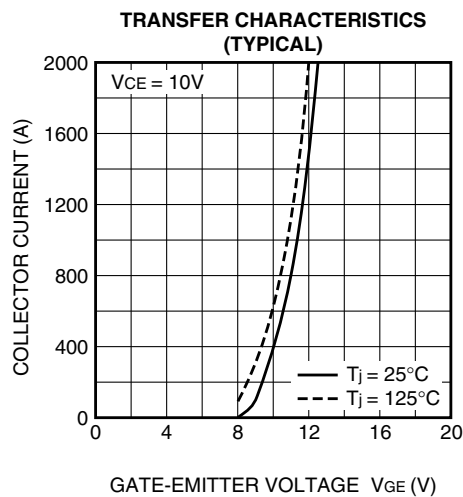
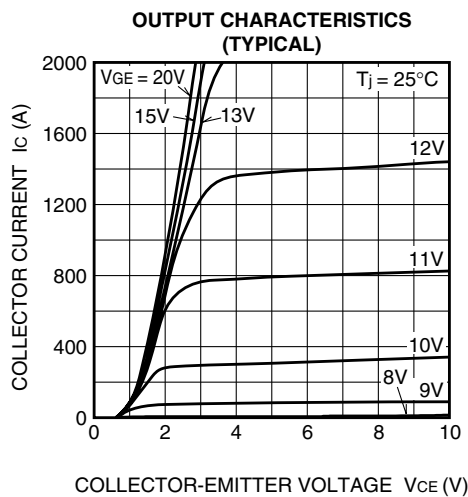
*3 : The operation temperature is restrained by the permission temperature of female connector.

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PERFORMANCE CURVES



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